CLAIMS

1. A plated substrate adapted for hard disk medium comprising

a Si single crystal substrate;

an amorphous layer on the substrate, the amorphous layer having thickness of 2 to 200nm and containing Si and one or more metals selected from a group consisting of Ni, Cu and Ag; and

a multicrystal layer on the amorphous layer, the multicrystal layer having thickness of 5 to 1000nm and containing Si and one or more metals selected from a group consisting of Ni, Cu and Ag.

2. A method for manufacturing a plated substrate adapted for hard disk medium comprising steps of:

applying a chemical etching treatment of a natural oxide film and a surface Si portion on an Si single crystal substrate, and

forming a film on the etched surface of the substrate in a sulfate or hydrochloride bath containing no reductant within a pH range of 7.2 to 12.8 at liquid temperature of 70 to 100°C.

3. The method for manufacturing a plated substrate adapted for hard disk medium according to Claim 2, wherein a heavy metal component in said sulfate bath is one or more selected from the group consisting of Ni, Cu and Ag.

4. The method for manufacturing a plated substrate adapted for hard disk medium according to Claim 2, wherein said pH range is controlled by an addition of ammonia.

5. The method for manufacturing a plated substrate adapted for hard disk medium according to Claim 3, wherein said pH range is controlled by an addition of ammonia.